

isc Silicon NPN Power Transistor

2SC4744

DESCRIPTION

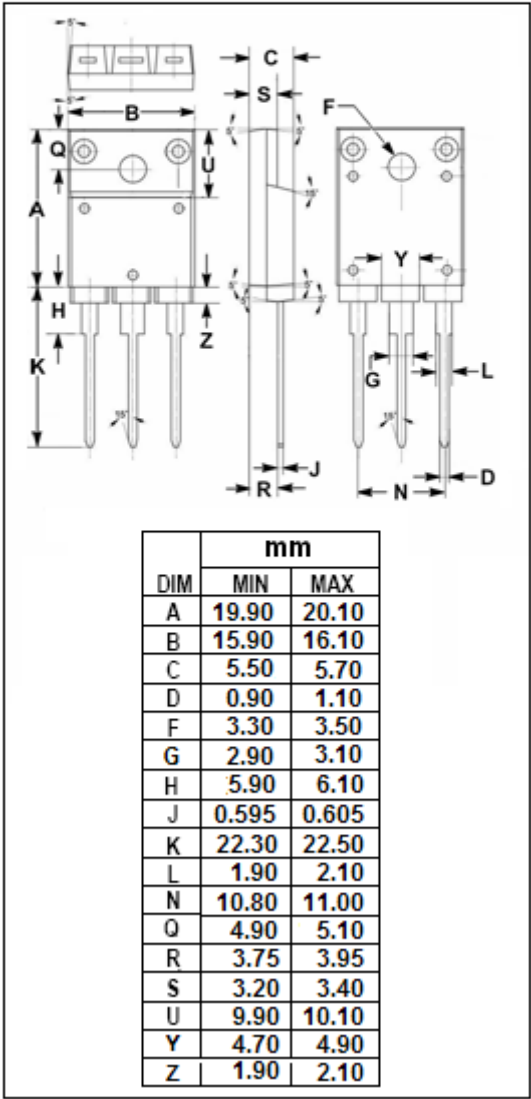
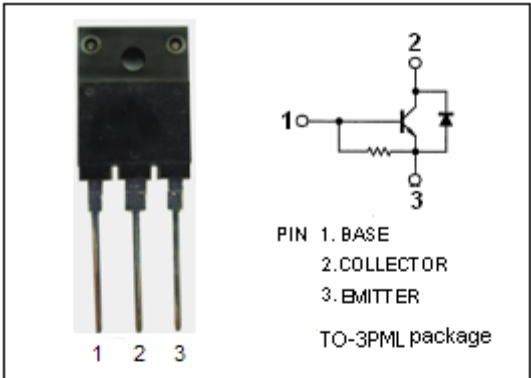
- High Breakdown Voltage-
: $V_{CBO}=1500V$ (Min)
- High Switching Speed
- Built-in Damper Diode

APPLICATIONS

- Designed for character display horizontal deflection
output stage applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
$I_{C(peak)}$	Collector Current-Peak	7	A
$I_{C(surge)}$	Collector Current-Surge	16	A
I_D	C-E Diode Forward Current	7	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$

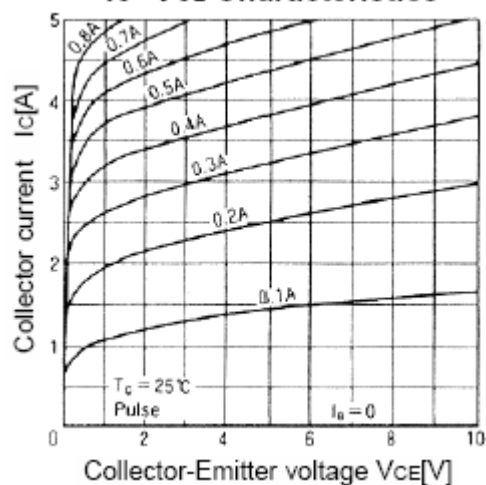
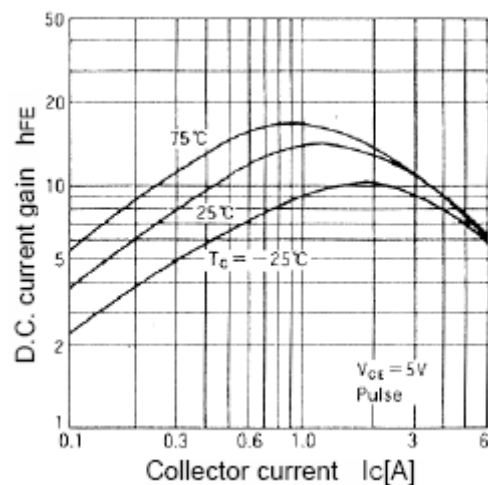
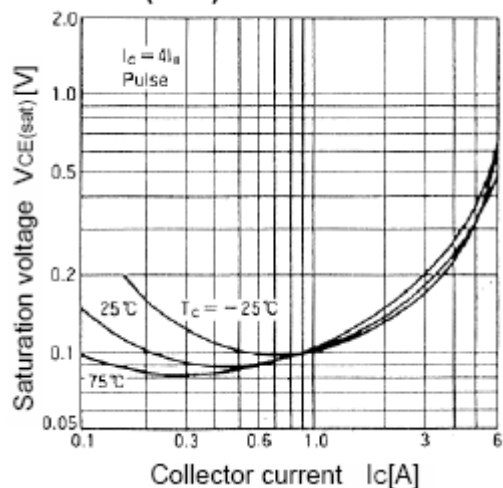
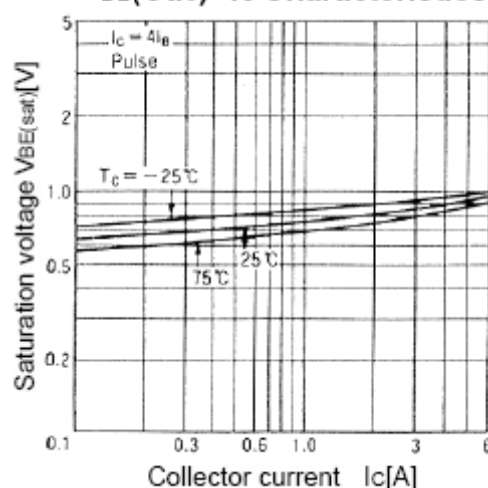


ISC Silicon NPN Power Transistor**2SC4744****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

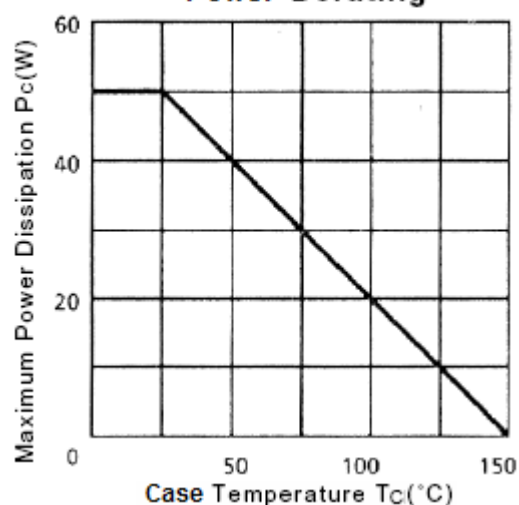
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 400mA ; I _C = 0	6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1.25A			2.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1.25A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} = 1500V ; R _{BE} = 0			500	μ A
h _{FE}	DC Current Gain	I _C = 1A ; V _{CE} = 5V			25	
V _{ECF}	C-E Diode Forward Voltage	I _F = 6A			2.0	V
t _f	Fall Time	I _{CP} = 5A , I _{B1} = 1A; I _{B2} = -2A			0.4	μ S

isc Silicon NPN Power Transistor

2SC4744

 I_C - V_{CE} Characteristics h_{FE} - I_C Characteristics $V_{CE(sat)}$ - I_C Characteristics $V_{BE(sat)}$ - I_C Characteristics

Power Derating



Safe Operating Area

